



# **PRODUCT DATA SHEET**



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Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.



## PESD3V3MS

LOW CAPACITANCE BIDIRECTIONAL TVS DIODE

#### Features

- Ultra-Small, Low Profile Leadless Surface Mount Package (0.6 x 0.3 x 0.3mm)
- Provides ESD Protection per IEC 61000-4-2 Standard: Air – ±30kV, Contact – ±25kV
- 1 Channel of ESD Protection
- Low Channel Input Capacitance
- Typically Used in Cellular Handsets, Portable Electronics, Communication Systems, Computers and Peripherals



DFN0603

#### **Mechanical Data**

- Case Material: Molded Plastic, "Green" Molding
  Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish –Matte Tin over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0002 grams (Approximate)



### **Device Schematic**

#### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	Conditions
Peak Pulse Power Dissipation	P <sub>PP</sub>	35	W	8/20µs, Per Fig. 3
Peak Pulse Current	IPP	5	A	8/20µs, Per Fig. 3
ESD Protection – Contact Discharge	V <sub>ESD_Contact</sub>	±25	kV	IEC 61000-4-2 Standard
ESD Protection – Air Discharge	$V_{ESD\_Air}$	±30	kV	IEC 61000-4-2 Standard

Ver.1.0



#### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Package Power Dissipation (Note 5)	PD	250	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	500	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-65 to +150	°C

#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
Reverse Standoff Voltage	V <sub>RWM</sub>	—	—	3.3	V	—
Channel Leakage Current (Note 6)	I <sub>RM</sub>		10	100	nA	V <sub>RWM</sub> = 3.3V
Clamping Voltage, Positive Transients	V <sub>CL</sub>		4.5 5.8	5.4 7.0	V	I <sub>PP</sub> = 1A, t <sub>P</sub> = 8/20µs I <sub>PP</sub> = 5A, t <sub>P</sub> = 8/20µs
Breakdown Voltage	V <sub>BR</sub>	3.8	—	6.5	V	I <sub>R</sub> = 1mA
Differential Resistance	R <sub>DIF</sub>	—	0.3	_	Ω	I <sub>R</sub> = 1A
Channel Input Capacitance	CT		10	13	pF	$V_R = 0V, f = 1MHz$







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### **Package Outline Dimensions**



X3-DFN0603-2				
Dim	Min	Max	Тур	
Α	0.27	0.35	0.30	
A1	0.00	0.03	0.02	
b	0.19	0.29	0.24	
D	0.595	0.645	0.62	
E	0.295	0.345	0.32	
е	-	-	0.355	
L	0.14	0.24	0.19	
All Dimensions in mm				



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